# N-Channel 150-V (D-S) MOSFET

# **Key Features:**

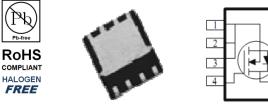
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
VDS (V)	$r_{DS(on)}(m\Omega)$	Id (A)	
150	360 @ V <sub>GS</sub> = 10V	3.1	
150	370 @ V <sub>GS</sub> = 4.5V	3.0	

#### DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage	V <sub>DS</sub>	150	V			
Gate-Source Voltage		V <sub>GS</sub>	±20	V		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I <sub>D</sub>	3.1			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C		2.5	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	15			
Continuous Source Current (Diode Conduction) <sup>a</sup>		ا <sub>s</sub>	5.6	А		
Device Direction a	T <sub>A</sub> =25°C	P <sub>D</sub>	5	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	ГD	3.2	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	25	°C/W		
	Steady State	ιν <sub>θ</sub> ja	65	C/vv		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 120 V, V_{GS} = 0 V$	1		1	uA	
	DSS	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	5			А	
Drain Source On Desistence a	r <sub>no</sub> ,	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.4 \text{ A}$			360	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 2 \text{ A}$			370	11152	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 2.4 \text{ A}$		29		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.84		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	$V_{DS} = 75 V, V_{GS} = 4.5 V,$		7.7			
Gate-Source Charge	Q <sub>gs</sub>	$v_{DS} = 75 \text{ V}, v_{GS} = 4.5 \text{ V},$ $I_{D} = 2.4 \text{ A}$		2.7		nC	
Gate-Drain Charge	$Q_{gd}$	10 - 2.4 A		3.3			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 75 V, R <sub>L</sub> = 31.3 Ω,		8			
Rise Time	t <sub>r</sub>	$V_{DS} = 73$ V, $R_{L} = 31.3$ G2, $I_{D} = 2.4$ A,		9		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		31			
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		9			
Input Capacitance	C <sub>iss</sub>			705			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		51		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			28			

#### Notes

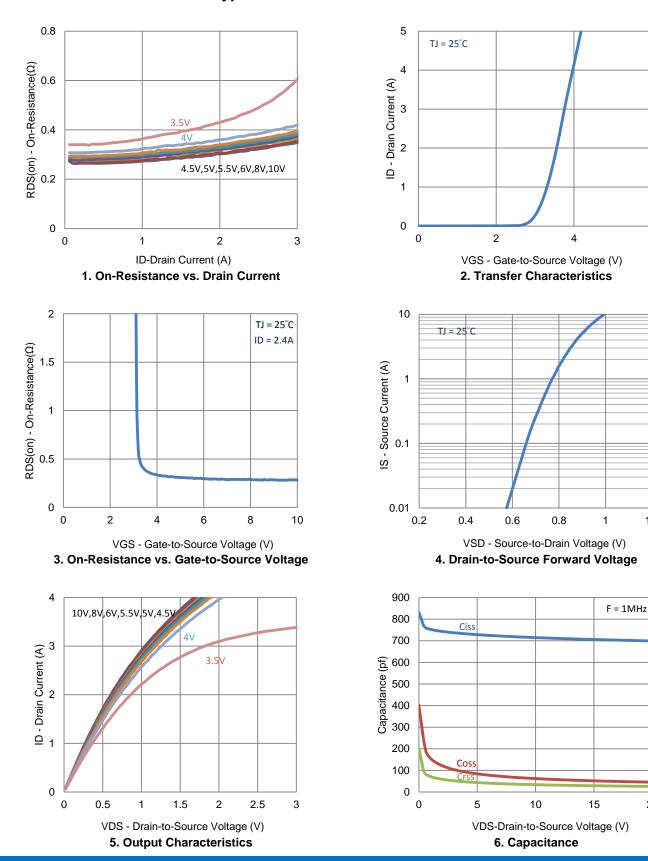
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

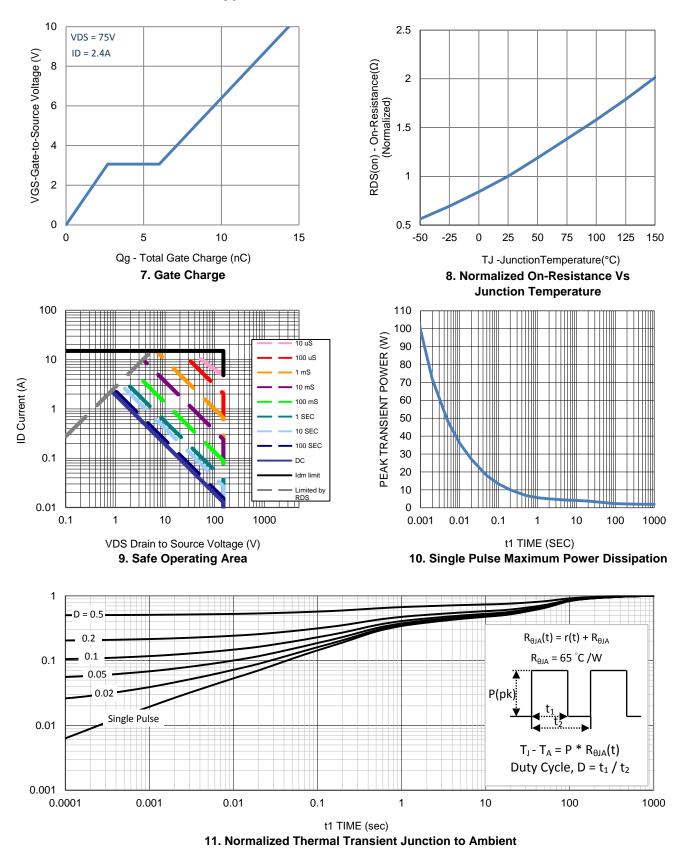
6

1.2

20

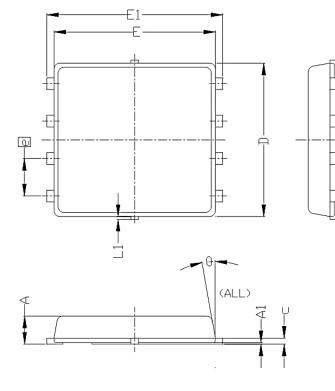


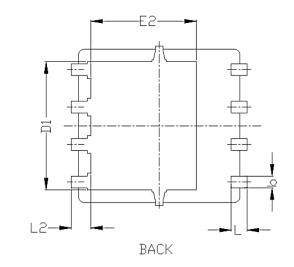
## **Typical Electrical Characteristics**



## **Typical Electrical Characteristics**

# Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES				
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.85	0.95	1.00	0.033	0.037	0.039		
Al	0.00		0.05	0.000		0.002		
b	0.30	0.40	0.50	0.012	0.016	0.020		
с	0.15	0.20	0.25	0.006	0.008	0.010		
D		5.20 BSC			0.205 BSC			
D1	4.35 BSC			0.171 BSC				
E		5, 55 BSC 0, 219 BSC						
E1	6.05 BSC			0.238 BSC				
E2	3.62 BSC			0. 143 BSC				
e	1.27 BSC			0.050 BSC				
L	0.45	0.55	0.65	0.018	0.022	0.026		
L1	0		0.15	0		0.006		
L2	0.68 REF			0.027 REF				
θ	0°		10°	0°		10°		